To all our customers

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The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HAT3004R

Silicon N Channel / P Channel Power MOS FET
High Speed Power Switching

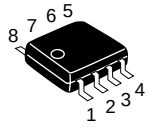
ADE-208-500I (Z)
10th. Edition
Aug. 1997

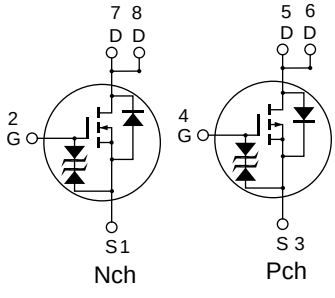
Features

- Low on-resistance
- Capable of 4 V gate drive
- Low drive current
- High density mounting

Outline

SOP–8





1, 3	Source
2, 4	Gate
5, 6, 7, 8	Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		Nch	Pch	
Drain to source voltage	V_{DSS}	30	–30	V
Gate to source voltage	V_{GSS}	±20	±20	V
Drain current	I_D	5.5	–3.5	A
Drain peak current	$I_{D(pulse)}$ Note1	44	–28	A
Body-drain diode reverse drain current	I_{DR}	5.5	–3.5	A
Channel dissipation	Pch Note2	2		W
Channel dissipation	Pch Note3	3		W
Channel temperature	Tch	150		°C
Storage temperature	Tstg	–55 to +150		°C

Note: 1. PW ≤ 10µs, duty cycle ≤ 1 %
2. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s
3. 2 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s

Electrical Characteristics (N channel) (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	I_D = 10mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16V, V_{DS} = 0
Zero gate voltege drain current	I_{DSS}	—	—	10	µA	V_{DS} = 30 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	V_{DS} = 10V, I_D = 1mA
Static drain to source on state resistance	$R_{DS(on)}$	—	0.050	0.065	Ω	I_D = 3A, V_{GS} = 10V Note4
	$R_{DS(on)}$	—	0.078	0.11	Ω	I_D = 3A, V_{GS} = 4V Note4
Forward transfer admittance	$\|y_{fs}\|$	3.5	5.5	—	S	I_D = 3A, V_{DS} = 10V Note4
Input capacitance	Ciss	—	310	—	pF	V_{DS} = 10V
Output capacitance	Coss	—	220	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	100	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	17	—	ns	V_{GS} = 4V, I_D = 3A
Rise time	t_r	—	190	—	ns	V_{DD} ÷ 10V
Turn-off delay time	$t_{d(off)}$	—	25	—	ns	
Fall time	t_f	—	60	—	ns	
Body–drain diode forward voltage	V_{DF}	—	0.9	1.4	V	IF = 5.5A, V_{GS} = 0 Note4
Body–drain diode reverse recovery time	t_{rr}	—	50	—	ns	IF = 5.5A, V_{GS} = 0 diF/ dt =20A/µs

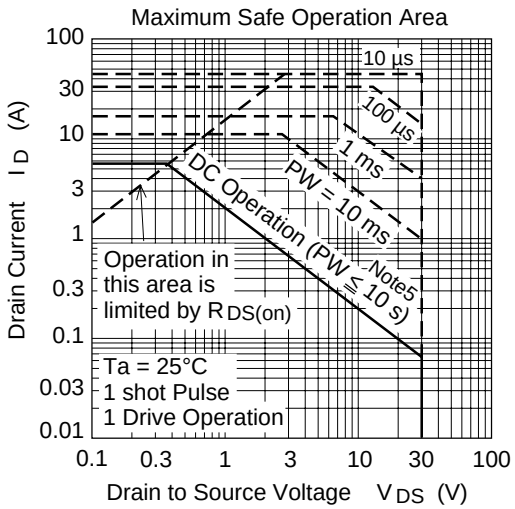
Note: 4. Pulse test

Electrical Characteristics (P channel) (Ta = 25°C)

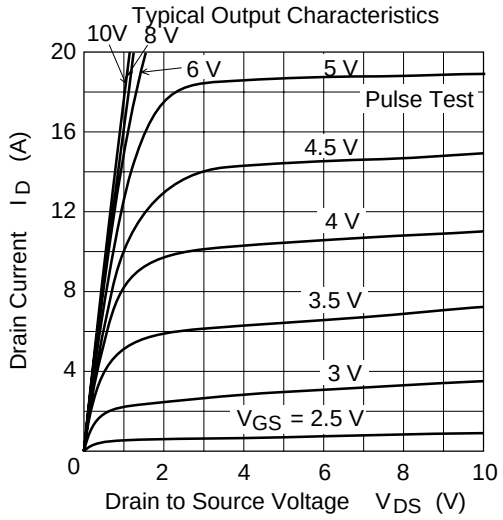
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	–30	—	—	V	I_D = –10mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16V, V_{DS} = 0
Zero gate voltege drain current	I_{DSS}	—	—	–10	µA	V_{DS} = –30 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	–1.0	—	–2.5	V	V_{DS} = –10V, I_D = –1mA
Static drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.16	Ω	I_D = –2A, V_{GS} = –10V Note5
	$R_{DS(on)}$	—	0.20	0.34	Ω	I_D = –2A, V_{GS} = –4V Note5
Forward transfer admittance	$\|y_{fs}\|$	2.5	3.5	—	S	I_D = –2A, V_{DS} = –10V Note5
Input capacitance	Ciss	—	350	—	pF	V_{DS} = –10V
Output capacitance	Coss	—	230	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	75	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	18	—	ns	V_{GS} = –4V, I_D = –2A
Rise time	t_r	—	110	—	ns	V_{DD} ÷ –10V
Turn-off delay time	$t_{d(off)}$	—	20	—	ns	
Fall time	t_f	—	30	—	ns	
Body–drain diode forward voltage	V_{DF}	—	–1.0	–1.5	V	IF = –3.5A, V_{GS} = 0 Note5
Body–drain diode reverse recovery time	t_{rr}	—	60	—	ns	IF = –3.5A, V_{GS} = 0 diF/ dt =20A/µs

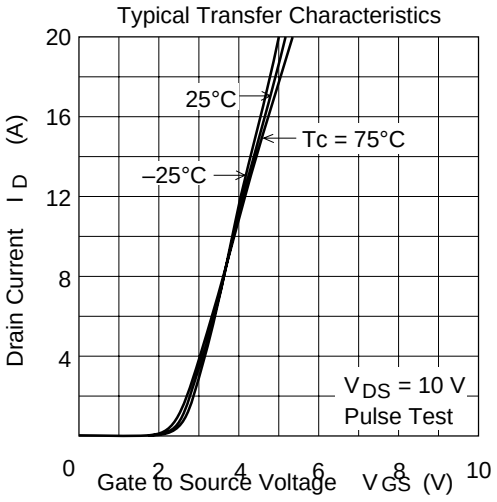
Note: 5. Pulse test

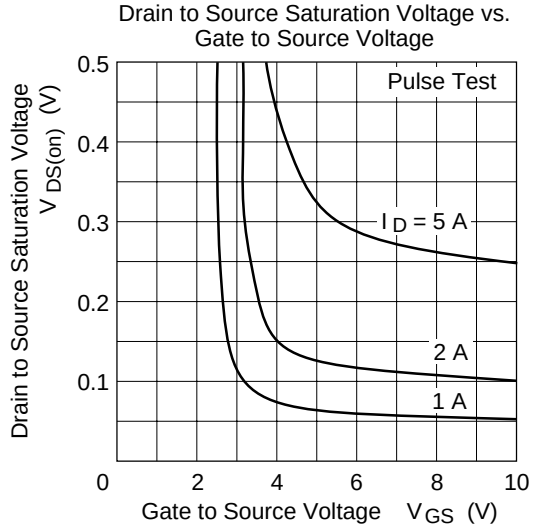
Main Characteristics (N channel)



Note 5 :
When using the glass epoxy board
(FR4 40x40x1.6 mm)

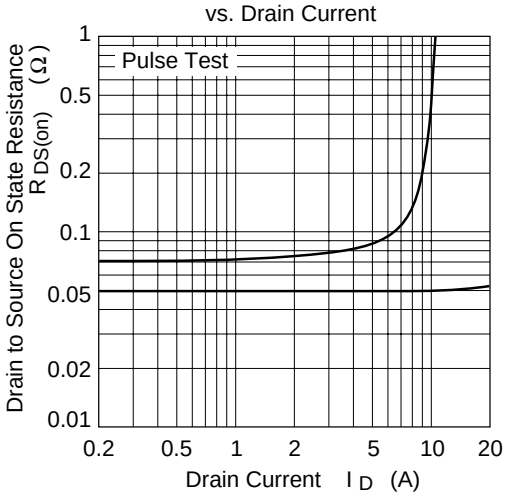




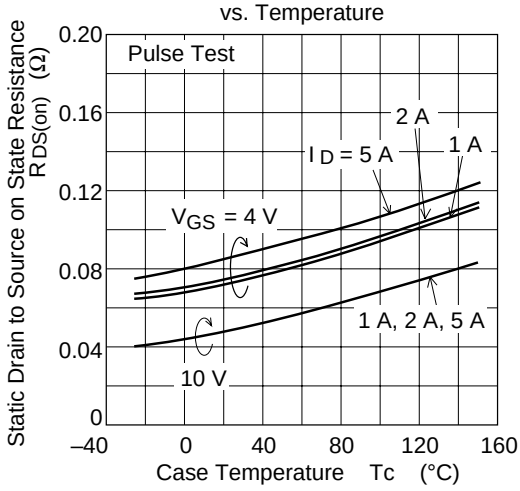


Main Characteristics (N channel)

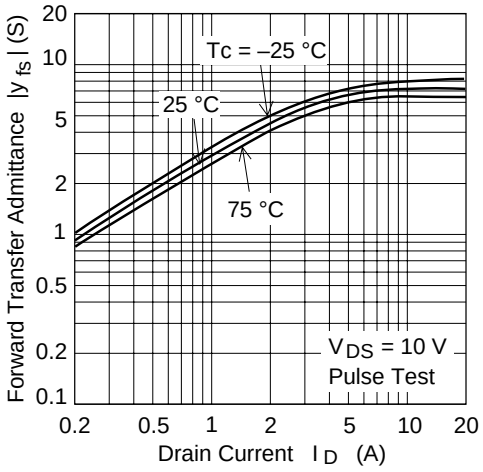
Static Drain to Source on State Resistance vs. Drain Current



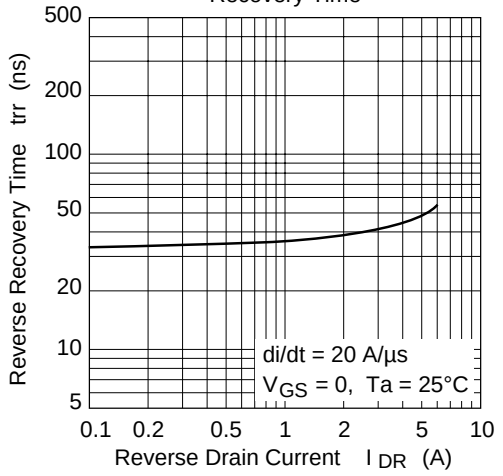
Static Drain to Source on State Resistance vs. Temperature



Forward Transfer Admittance vs. Drain Current

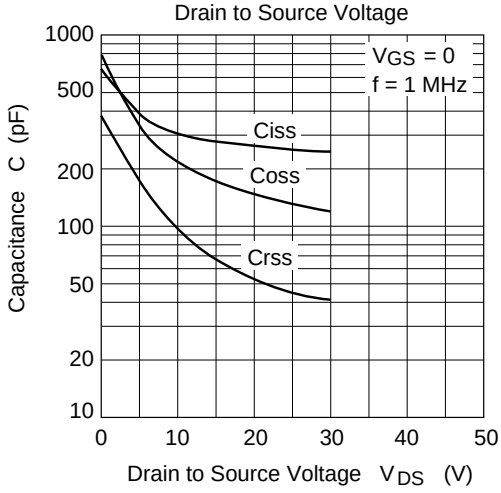


Body–Drain Diode Reverse Recovery Time

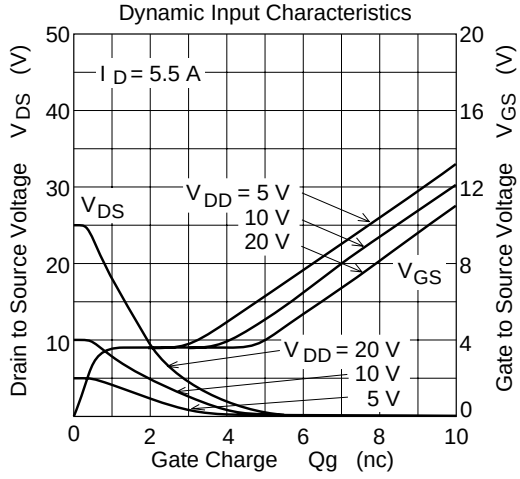


Main Characteristics (N channel)

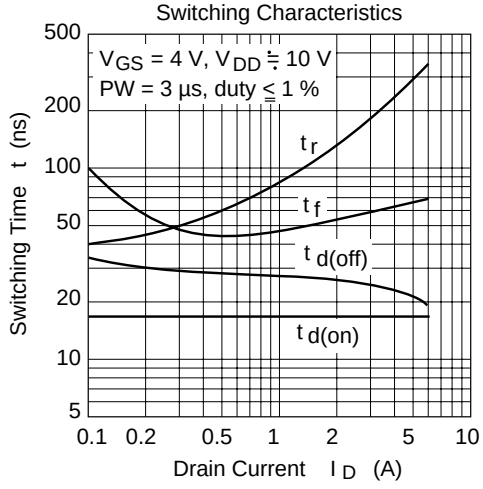
Typical Capacitance vs.
Drain to Source Voltage



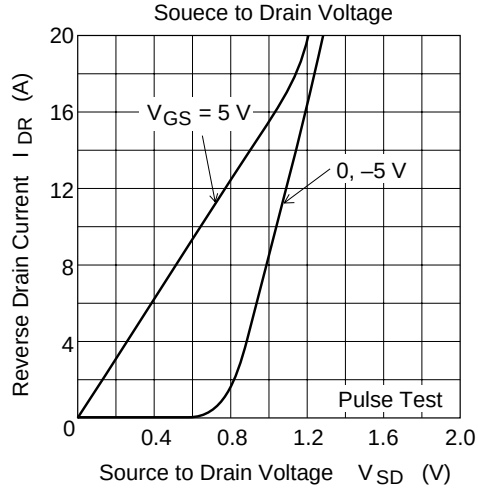
Dynamic Input Characteristics



Switching Characteristics

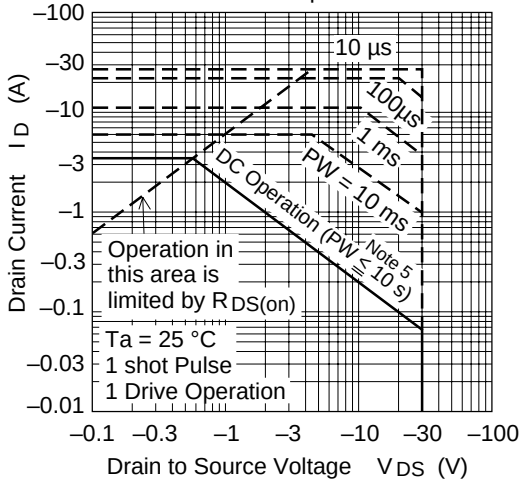


Reverse Drain Current vs.
Souece to Drain Voltage

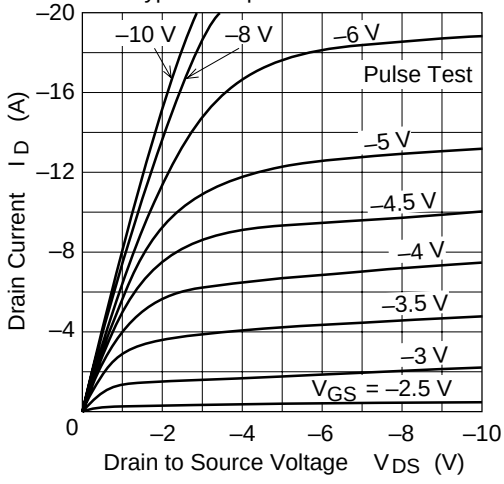


Main Characteristics (P channel)

Maximum Safe Operation Area

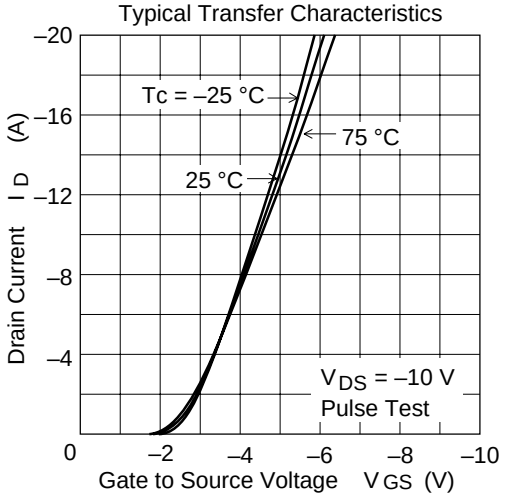


Typical Output Characteristics

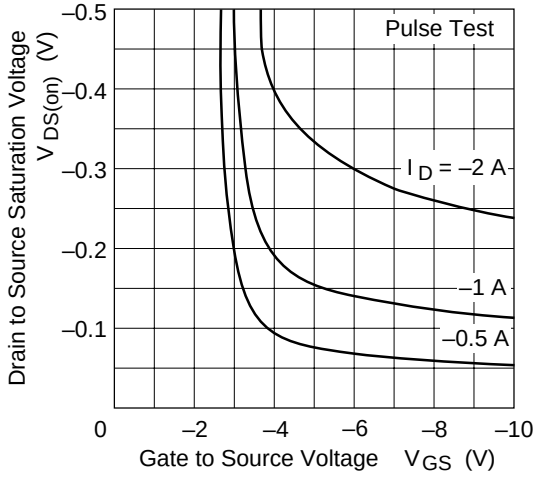


Note 5 :
When using the glass epoxy board
(FR4 40x40x1.6 mm)

Typical Transfer Characteristics

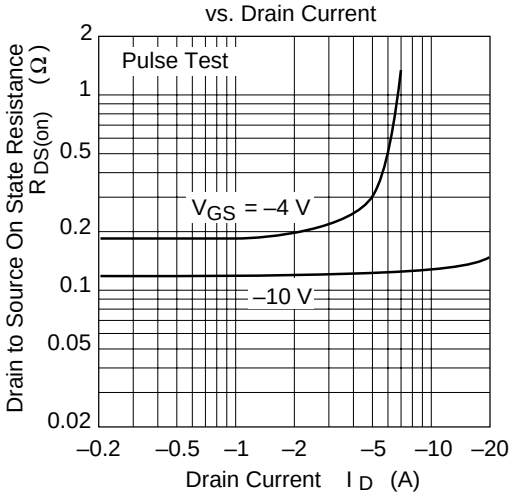


Drain to Source Saturation Voltage vs. Gate to Source Voltage

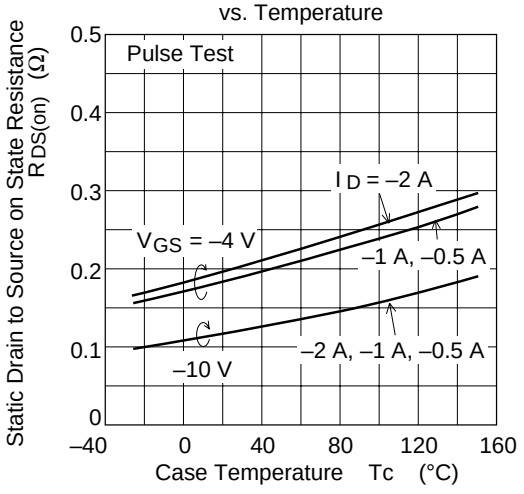


Main Characteristics (P channel)

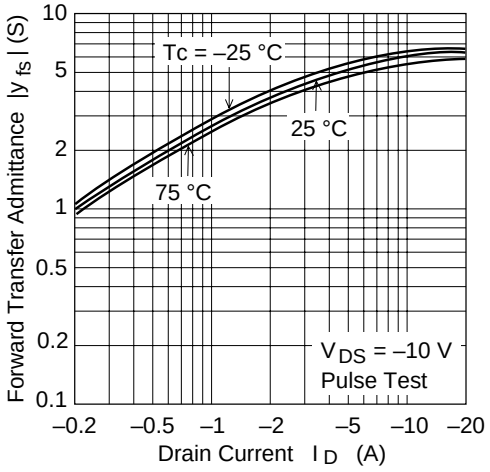
Static Drain to Source on State Resistance vs. Drain Current



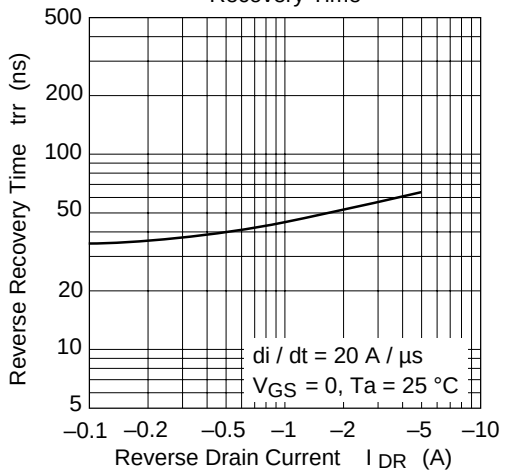
Static Drain to Source on State Resistance vs. Temperature



Forward Transfer Admittance vs. Drain Current

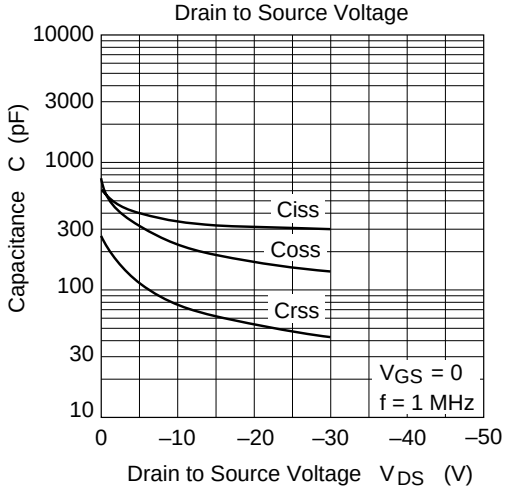


Body–Drain Diode Reverse Recovery Time

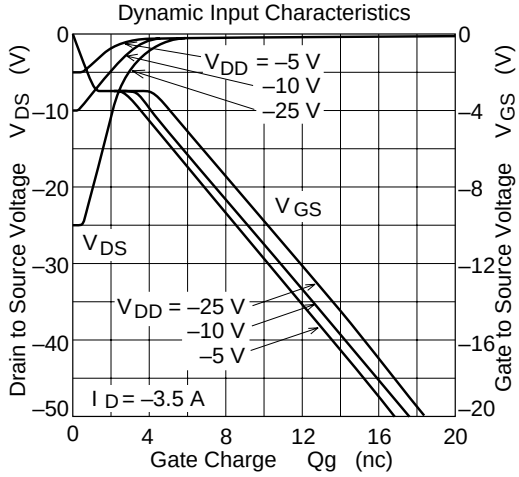


Main Characteristics (P channel)

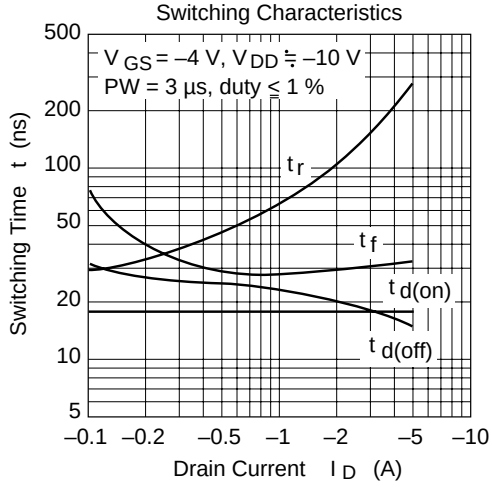
Typical Capacitance vs.
Drain to Source Voltage



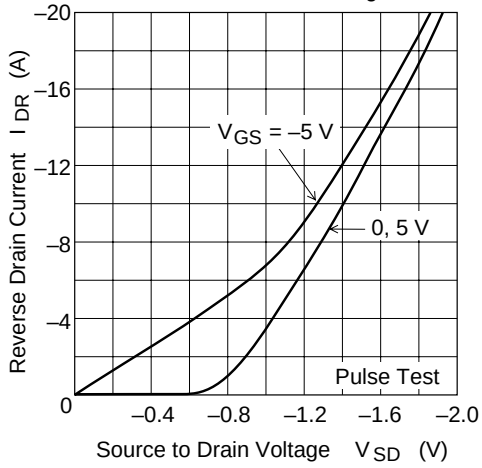
Dynamic Input Characteristics

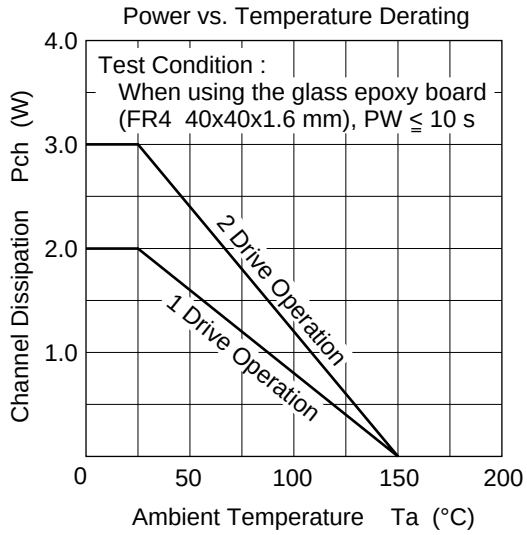


Switching Characteristics

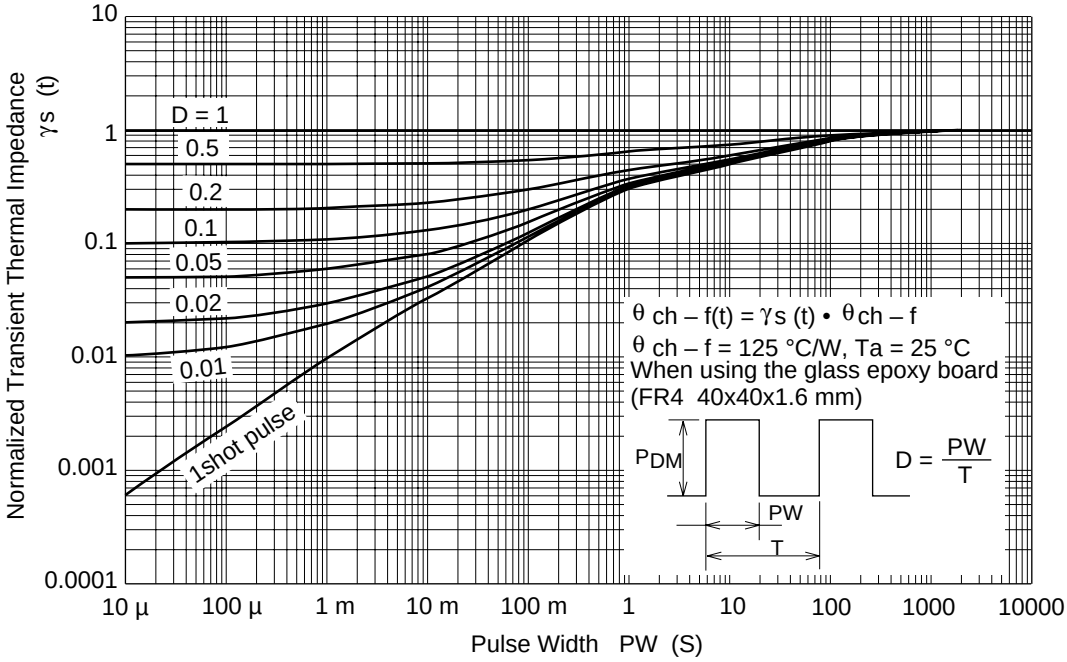


Reverse Drain Current vs.
Souece to Drain Voltage

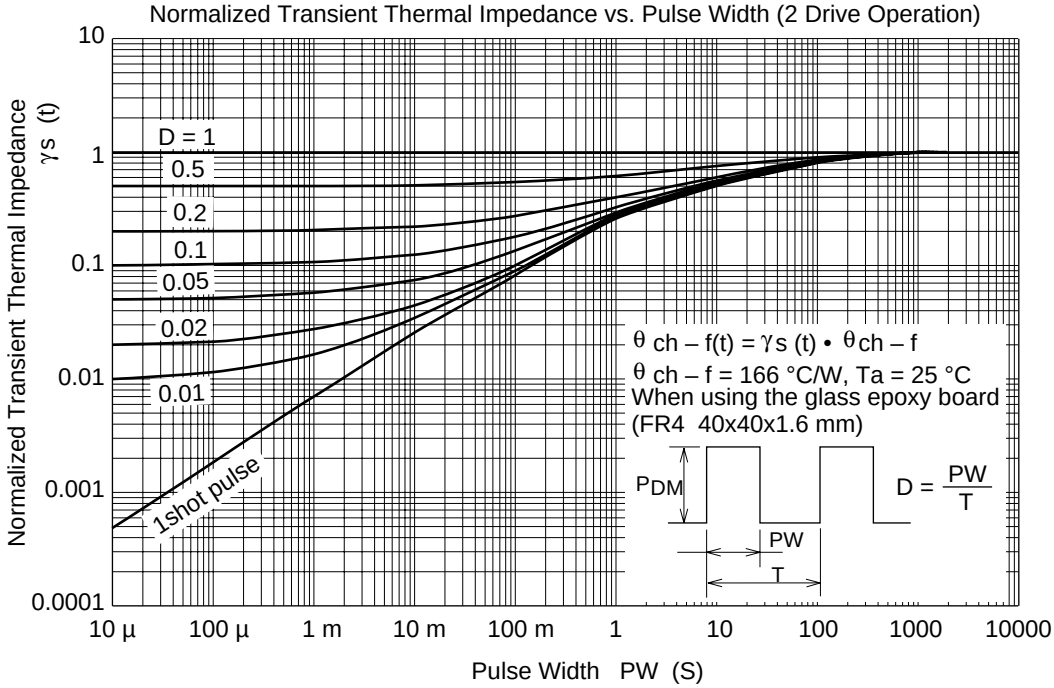



Power vs. Temperature Derating
Test Condition :
When using the glass epoxy board
(FR4 40x40x1.6 mm), PW ≦ 10 s
Channel Dissipation Pch (W)
4.0
3.0
2.0
1.0
0
50
100
150
200
2 Drive Operation
1 Drive Operation
Ambient Temperature Ta (°C)

Normalized Transient Thermal Impedance vs. Pulse Width (1 Drive Operation)

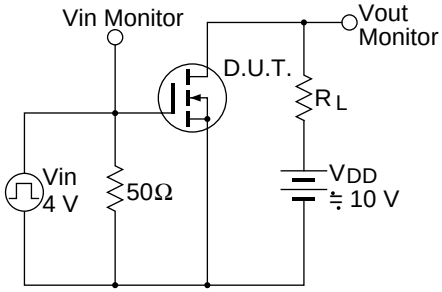


Normalized Transient Thermal Impedance vs. Pulse Width (2 Drive Operation)

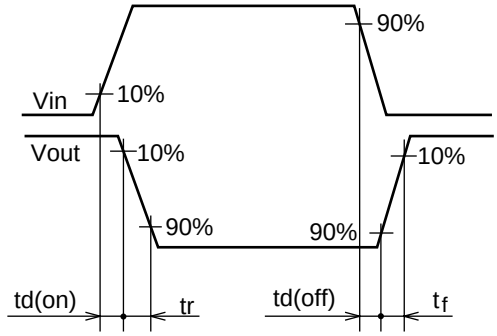


N channel

Switching Time Test Circuit

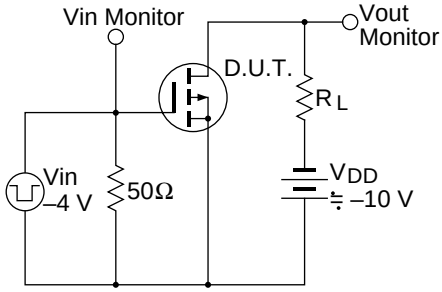


Switching Time Waveform

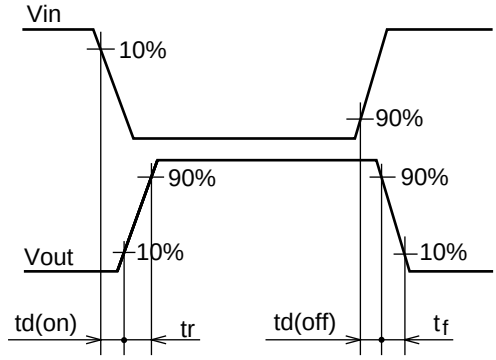


P channel

Switching Time Test Circuit



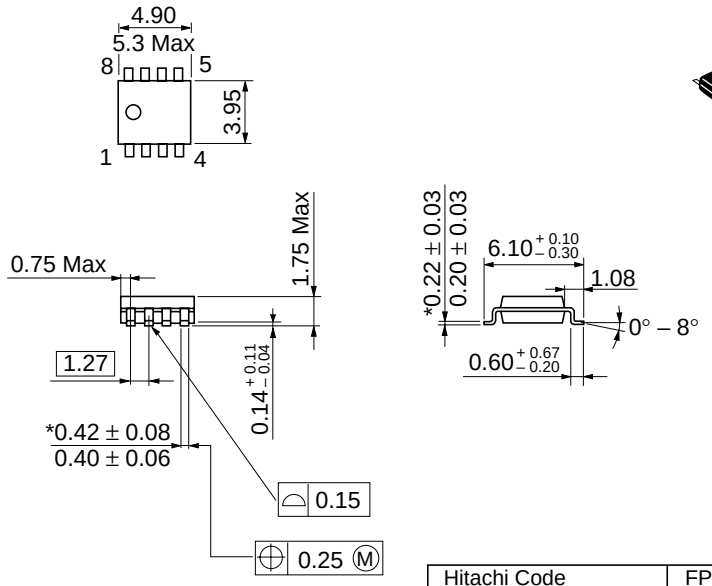
Switching Time Waveform



Package Dimensions

As of January, 2001

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-8DA
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.085 g

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